

Amendments to the Specification:

Please amend paragraph [0028] on page 17 of the specification as follows:

--The embodiment of the present invention will be described based on Fig. 5. While continuously feeding SiH_2Cl_2 at a partial pressure of 10 sccm, C_2H_2 was intermittently fed to grow silicon carbide. The partial pressure of the SiH_2Cl_2 was 10 sccm. C_2H_2 was intermittently fed 1,000 times at intervals of 5 sec at a partial pressure of 10 sccm. Each time, the C_2H_2 was fed for 5 sec. Growth of silicon carbide required 2.8 hour. As a result of the growth, $67\text{ }\mu\text{m}$ of single crystal silicon carbide was obtained on the silicon substrate. The effective growth rate of silicon carbide was $24\text{ }\mu\text{m/hr}$. Further, surface defects such as anti phase boundaries and twin crystal bands had been eliminated from the surface of the crystal obtained. In this manner, the use of the present invention permitted an accelerated rate of silicon carbide growth exceeding $10\text{ }\mu\text{m/hr}$ and permitted a substantial decrease in crystal defects. (~~$\text{fc}_2/\text{fs}=4\text{xSs}/\text{Sc}$, $\text{fc}_1=0$, that is $\text{pc}_2/\text{ps}=4\text{xSx}/\text{Sc}$, $\text{pc}_1=0$~~) ($\text{fc}_1/\text{fs}=4\text{xSs}/\text{Sc}$, $\text{fc}_2=0$, that is $\text{pc}_1/\text{ps}=4\text{xSx}/\text{Sc}$, $\text{pc}_2=0$).

Please amend paragraph [0031] on page 18 of the specification as follows:

The embodiment of the present invention will be described based on Fig. 6 below. While continuously feeding SiH_2Cl_2 at a flow rate of 10 sccm, C_2H_2 was intermittently fed to grow silicon carbide. The SiH_2Cl_2 flow rate was a constant 10 sccm. C_2H_2 was intermittently fed 1,000 times at intervals of 5 sec. Each time, C_2H_2 was fed for 5 sec. However, the flow rate fc of C_2H_2 was treated as a parameter and fc_2 was varied from 0.5-200 sccm and the change in silicon carbide growth was observed. (~~$\text{fc}_2/\text{fs}=4\text{xSs}/\text{Sc}$, $\text{fc}_1=0$, that is $\text{pc}_2/\text{ps}=4\text{xSx}/\text{Sc}$, $\text{pc}_1=0$~~) ($\text{fc}_1/\text{fs}=4\text{xSs}/\text{Sc}$, $\text{fc}_2=0$, that is $\text{pc}_1/\text{ps}=4\text{xSx}/\text{Sc}$, $\text{pc}_2=0$).

Please amend the first paragraph on page 19 of the specification as follows:

Table 1 shows the changes in growth rates of silicon carbide by fc_2/fs fc_1/fs . When fc_2/fs fc_1/fs (that is, pc_2/ps pc_1/ps) was Ss/Sc (0.25) or greater, the growth rate of silicon carbide exceeded $10 \mu\text{m/hr}$ and the effect of the present invention was apparent. However, when fc_2/fs fc_1/fs (that is, pc_2/ps pc_1/ps) was less than Ss/Sc (0.25), not only did the growth rate of silicon carbide decrease, but silicon precipitated in the silicon carbide, precluding the effect of the present invention. Further, when fc_2/fs fc_1/fs (that is, pc_2/ps pc_1/ps) exceeded 2.5, the level of adsorption of C_2H_2 on the substrate surface increased. Since adsorption of SiH_2Cl_2 was blocked, the growth rate of silicon carbide dropped precipitously, precluding the effect of the present invention. Silicon carbide grown at an fc_2/fs fc_1/fs of not less than 0.15 and not greater than 3.5 did not exhibit surface defects such as anti phase boundaries and twin crystals.

Please delete the heading of Table 1 on page 20 of the specification in favor of the following new heading:

fc_1 (sccm)	fc_1/fs (pc_1/ps)	silicon carbide growth rate ($\mu\text{m/hr}$)
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Please amend paragraph [0035] on page 21 of the specification as follows:

The embodiment of the present invention will be described based on Fig. 7 below. While continuously feeding $SiCl_4$ at a flow rate of 20 sccm, C_3H_6 was intermittently fed to grow silicon carbide. C_3H_6 was fed 1,000 times at intervals of 5 sec, each time lasting 5 sec. However, the flow rate fc of C_3H_6 was treated as a parameter and fc_2/fs fc_1 was varied from 0.5-200 sccm and the change in silicon carbide growth was observed ($fc_1=0$, that is, $pc_1=0$) ($fc_2=0$, that is, $pc_2=0$).

Please amend the first paragraph on page 22 of the specification as follows:

Table 2 shows the changes in growth rates of silicon carbide by ~~fc2/fs~~ fc1. When ~~fc2/fs~~ fc1/fs (that is, ~~pc2/ps~~ pc1/ps) was Ss/Sc (0.68) or greater, the growth rate of silicon carbide exceeded 10 $\mu\text{m/hr}$ and the effect of the present invention was marked. However, when ~~fc2/fs~~ fc1/fs (that is, ~~pc2/ps~~ pc1/ps) was less than Ss/Sc (0.68), not only did the growth rate of silicon carbide decrease, but silicon precipitated in the silicon carbide, precluding the effect of the present invention. Further, when ~~fc2/fs~~ fc1/fs (that is, ~~pc2/ps~~ pc1/ps) exceeded 6.8, the level of adsorption of C_2H_5 on the substrate surface increased. Since adsorption of SiCl_4 was blocked, the growth rate of silicon carbide dropped precipitously, precluding the effect of the present invention.

Please amend the second paragraph on page 22 of the specification as follows:

Silicon carbide grown at an ~~fc2/fs~~ fc1/fs (that is, ~~pc2/ps~~ pc1/ps) of not less than 0.2 and not greater than 5 did not exhibit surface defects such as anti phase boundaries and twin crystals.

Please delete the heading of Table 2 on page 23 pf the specification in favor of the following new heading:

fc1 (sccm)	fc1/fs (pc1/ps)	silicon carbide growth rate ($\mu\text{m/hr}$)
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Please amend paragraph [0040] on page 24 of the specification as follows:

The embodiment of the present invention will be described based on Fig. 8 below. While continuously feeding SiH_2Cl_2 , C_2H_2 was intermittently fed to grow silicon carbide. The C_2H_2 flow rate (~~fc2~~) (fc1) was a constant 10 sccm (~~fc1=0, that is, pc1=0~~) (fc2=0, that is, pc2=0). C_2H_2 was intermittently fed 1,000 times at intervals of 5 sec for 5 sec each time. However, the flow

rate f_s of SiH_2Cl_2 was treated as a parameter and f_s was varied from 15 sccm to 200 sccm and the change in silicon carbide growth was observed.

Please amend the first paragraph on page 25 of the specification as follows:

Table 3 shows the changes in growth rates of silicon carbide by fgs. When f_{c2}/f_s f_{c1}/f_s (that is, p_{c2}/p_s p_{c1}/p_s) was S_s/S_c (0.25) or greater, the growth rate of silicon carbide exceeded $10 \mu\text{m/hr}$ and the effect of the present invention was apparent. However, when f_{c2}/f_s f_{c1}/f_s (that is, p_{c2}/p_s p_{c1}/p_s) was less than S_s/S_c (0.25), not only did the growth rate of silicon carbide decrease, but silicon precipitated in the silicon carbide, precluding the effect of the present invention. Further, when f_{c2}/f_s f_{c1}/f_s (that is, p_{c2}/p_s p_{c1}/p_s) exceeded 2.5, the level of adsorption of C_2H_2 on the substrate surface increased. Since adsorption of SiH_2Cl_2 was blocked, the growth rate of silicon carbide dropped precipitously, precluding the effect of the present invention.

Please amend the second paragraph on page 25 of the specification as follows:

Silicon carbide grown at an f_{c2}/f_s f_{c1}/f_s (that is, p_{c2}/p_s p_{c1}/p_s) of not less than 0.2 and not greater than 10 did not exhibit surface defects such as anti phase boundaries and twin crystals.

Please delete the heading of Table 3 on page 26 pf the specification in favor of the following new heading:

f_{c1} (sccm)	f_{c1}/f_s (p_{c1}/p_s)	silicon carbide growth rate ($\mu\text{m/hr}$)
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Please amend paragraph [0045] on pages 27 and 28 of the specification as follows:

The embodiment of the present invention will be described based on Fig. 9 below. While

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continuously feeding SiH_2Cl_2 , C_2H_2 was intermittently fed to grow silicon carbide. The SiH_2Cl_2 flow rate was a constant 10 sccm, and the C_2H_2 flow rate ~~(fc2)~~ (fc1). C_2H_2 was a constant 10 accm ~~(fc1=0, that is pc1=0)~~ (fc2=0, that is pc2=0). C_2H_2 was repeatedly fed 1,000 times at intervals of 5 sec. However, the time during which C_2H_2 was fed each time, denoted as t_c , was taken as a parameter and varied from 0 sec to 60 sec, and the change in silicon carbide growth rate was observed.